



PD24



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# Current status and development of of Digital CMOS SiPM

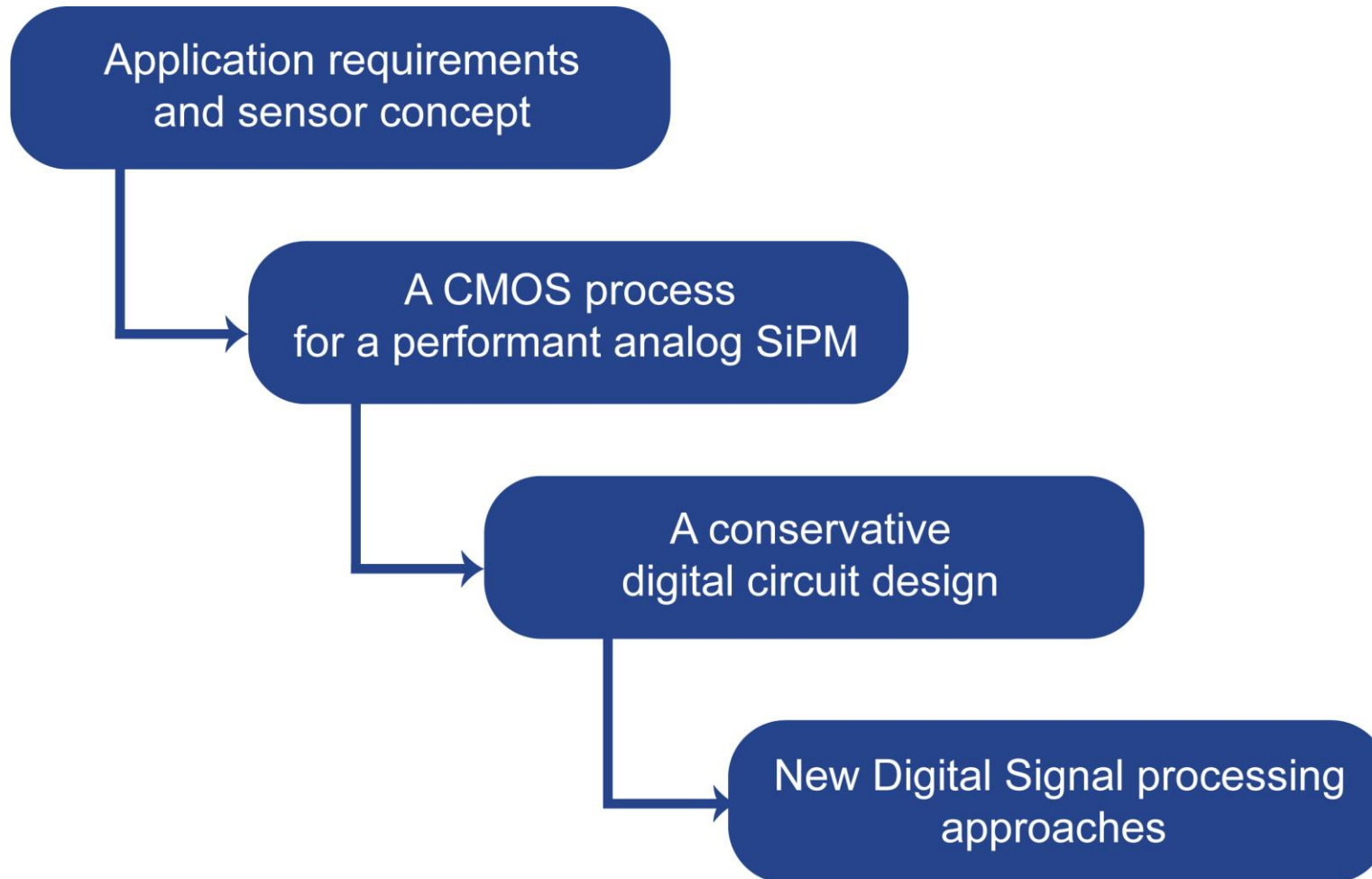
for scintillation-based detectors towards All-Digital sensors

Prof. Dr. Nicola D'Ascenzo

November 20<sup>th</sup> 2024



## A constructive-disruptive approach to new scintillator-based radiation detectors





## A constructive-disruptive approach to new scintillator-based radiation detectors

Application requirements  
and sensor concept

*Real-time portable Positron Emission Tomography for **agriculture** sets a high demanding standard to **high spatial resolution** and **fast timing** digital sensors*

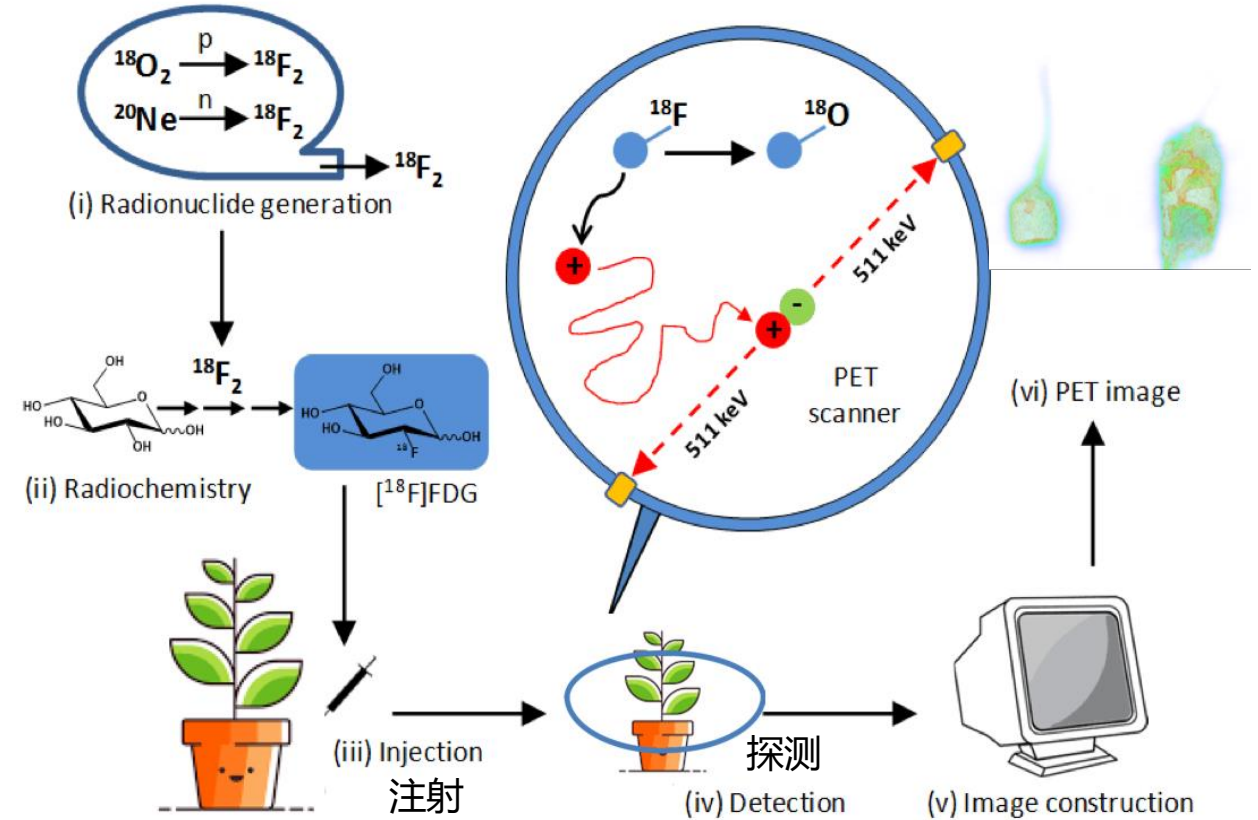
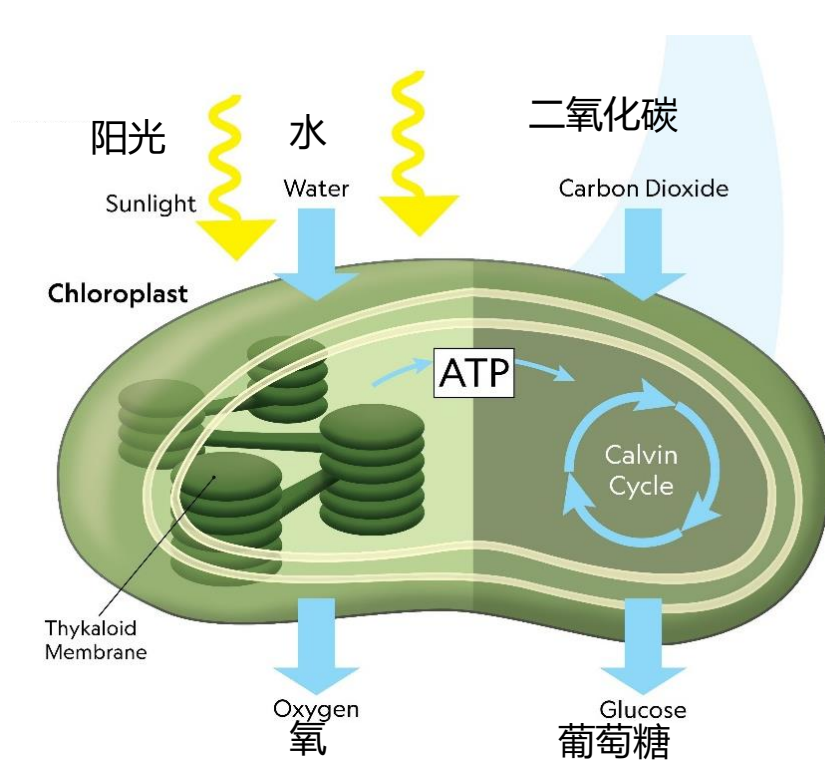
A CMOS process  
for a performant analog SiPM

A conservative  
digital circuit design

New Digital Signal processing  
approaches

# PET in agriculture

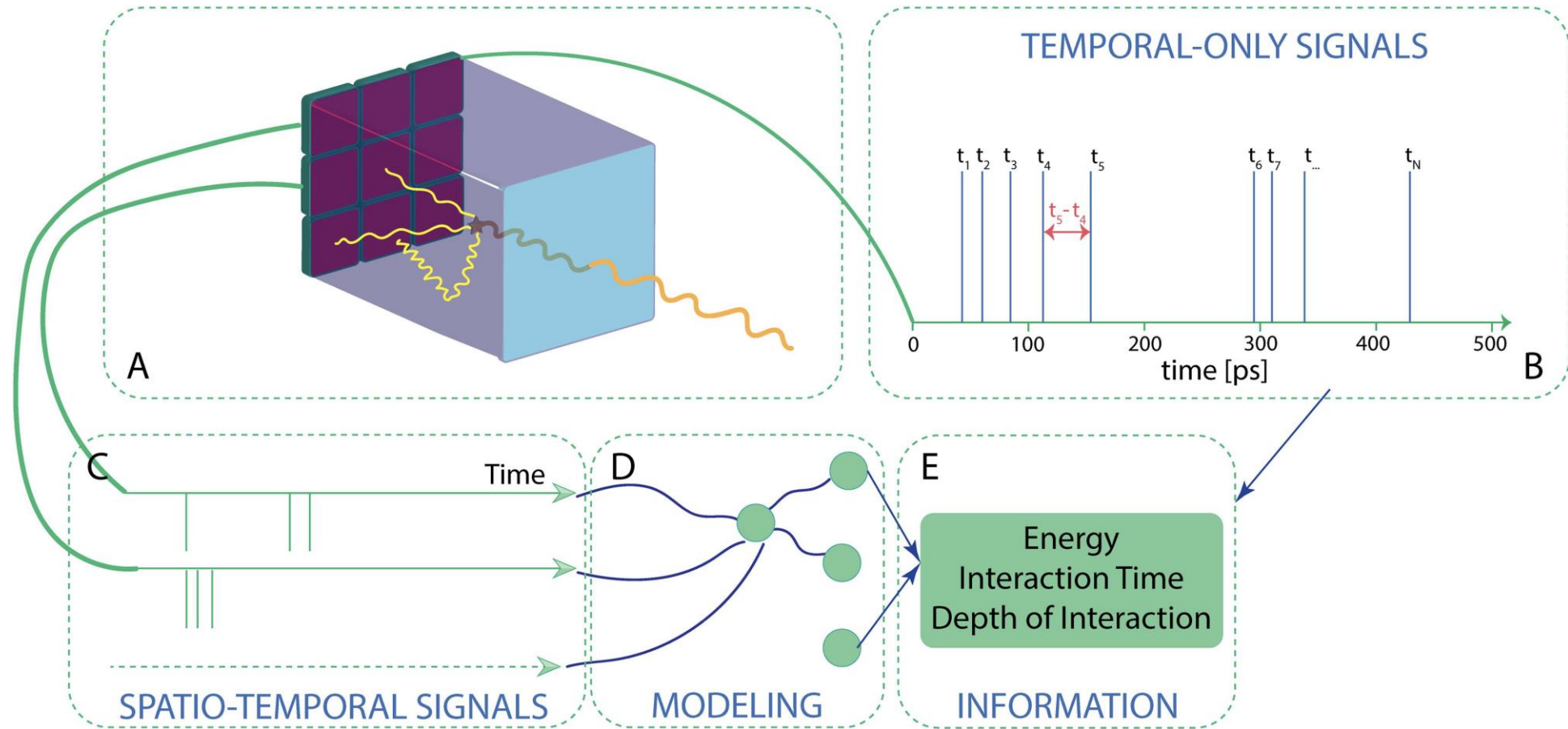
Quantify plants metabolism for the precise administration of Nitrogen fertilizers to reduce soil deterioration



Low energy gamma ray detectors, requiring spatial resolution  $< 0.5$  mm and timing resolution  $< 100$  ps

# The detector concept

Timing accuracy at 100 ps level and impact localization at 1 mm level are necessary in scintillation/sensor detectors



Space-time information of the scintillation optical photons enables new digital signal processing approaches

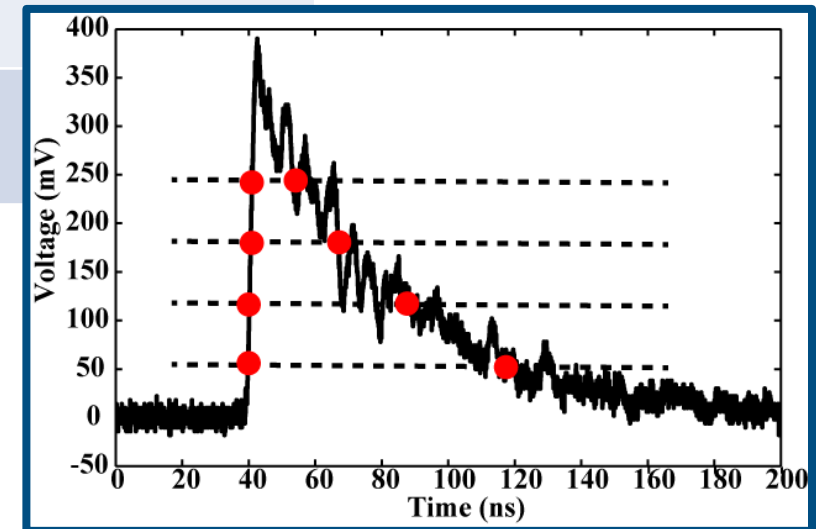
# SiPM target goals



The target parameters to be achieved in order to guarantee a proper readout of scintillation light

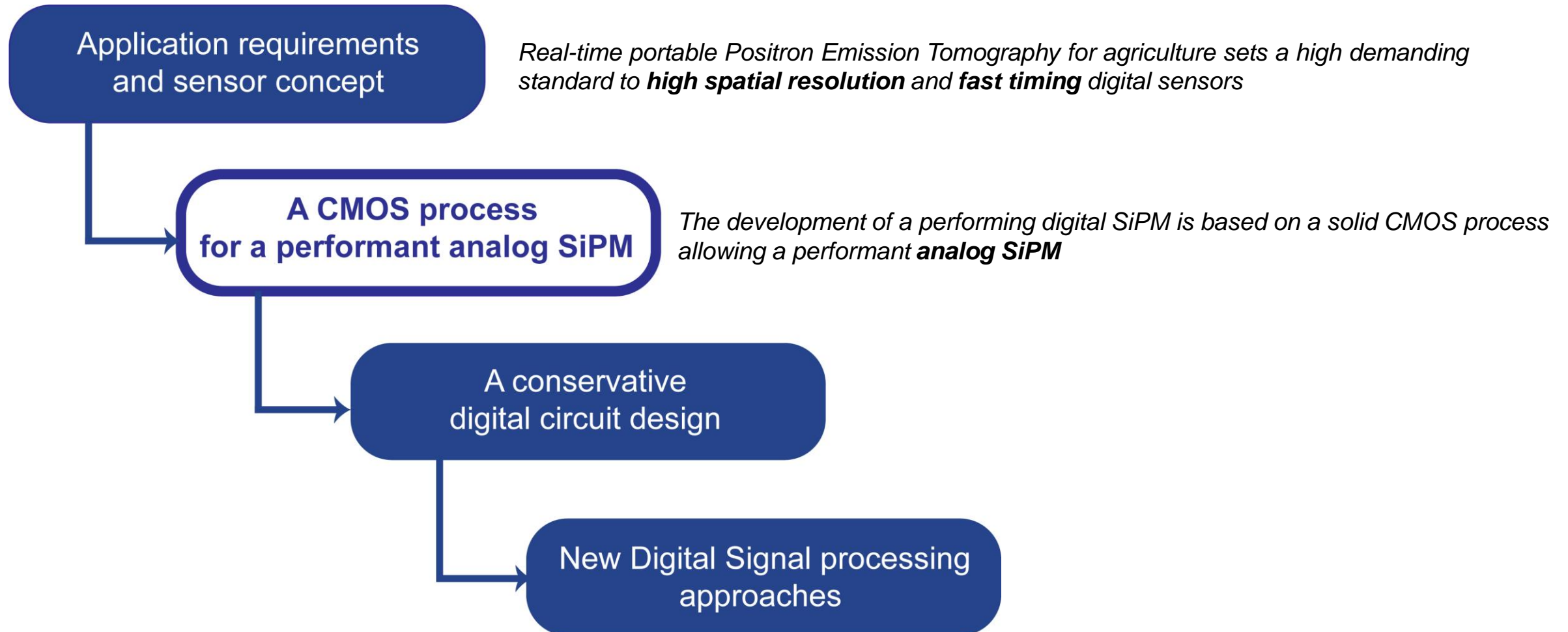
Observable	Parameter	Value
Integral	PDE	>40%@420 nm
	PDE	Possibly extendable below 350 nm
Temporal	SPTR	<100 ps
	PDE	>40%@420 nm
	DCR	<150 kcps/mm <sup>2</sup>
Spatiotemporal	Frame Rate	>5 MHz for 4x4 mm <sup>2</sup>
	Microcell pitch	<50 μm

$$R_E = 2.35 \frac{\sigma}{E} = 2.35 \sqrt{\frac{\sigma_{intr}^2}{E_\gamma^2} + \frac{1}{LY \times PDE \times E_\gamma \times \epsilon_{opt}}}$$



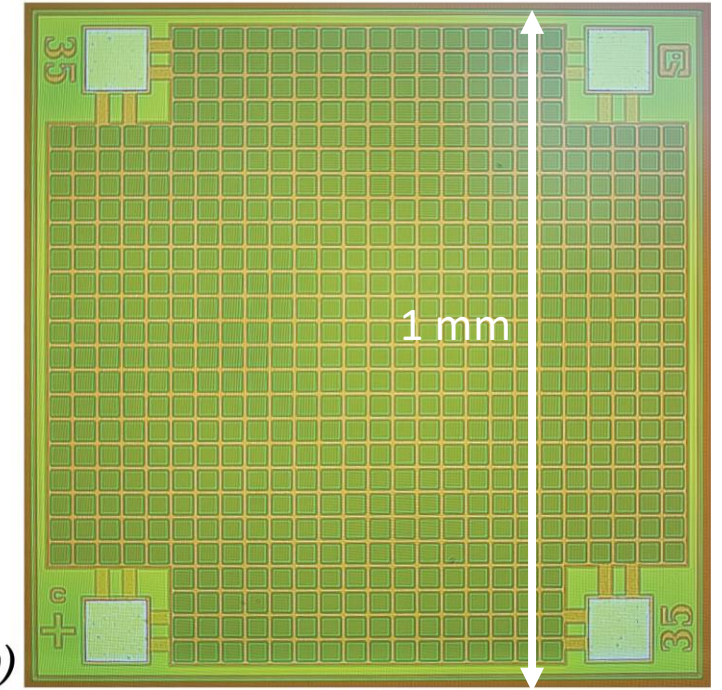
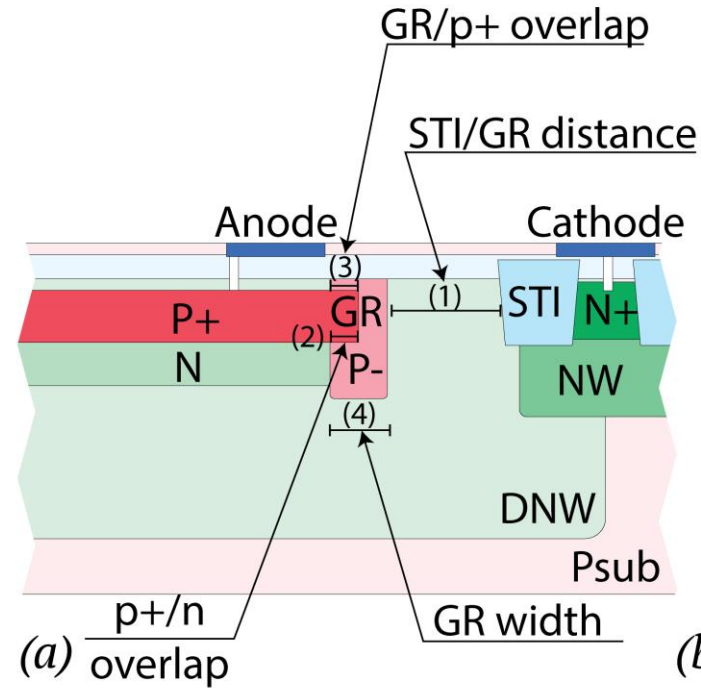
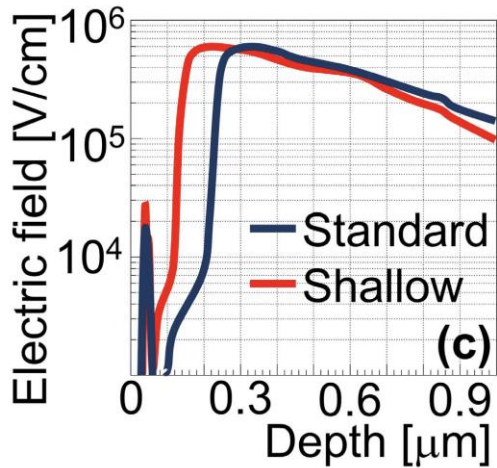
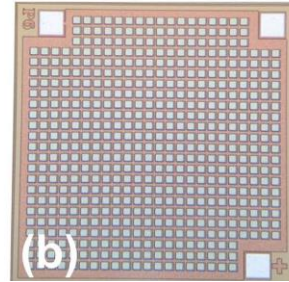
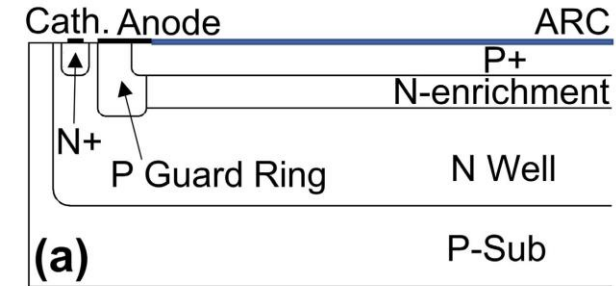


## A constructive-disruptive approach to new scintillator-based radiation detectors



# PDE: shallow junction

The path towards high PDE at the 420 nm spectral region is achieved by forming a shallow p/n junction



43% @ 420 nm 350 nm CMOS (2019)

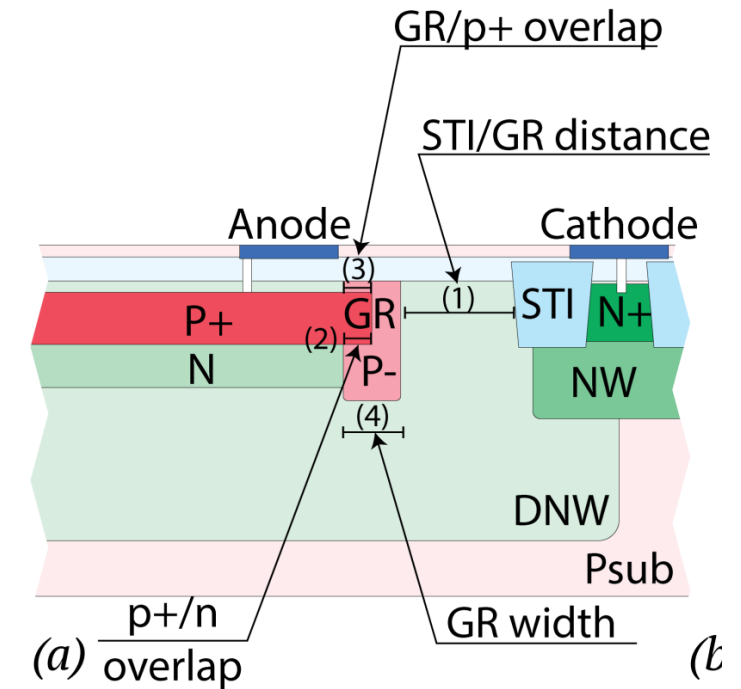
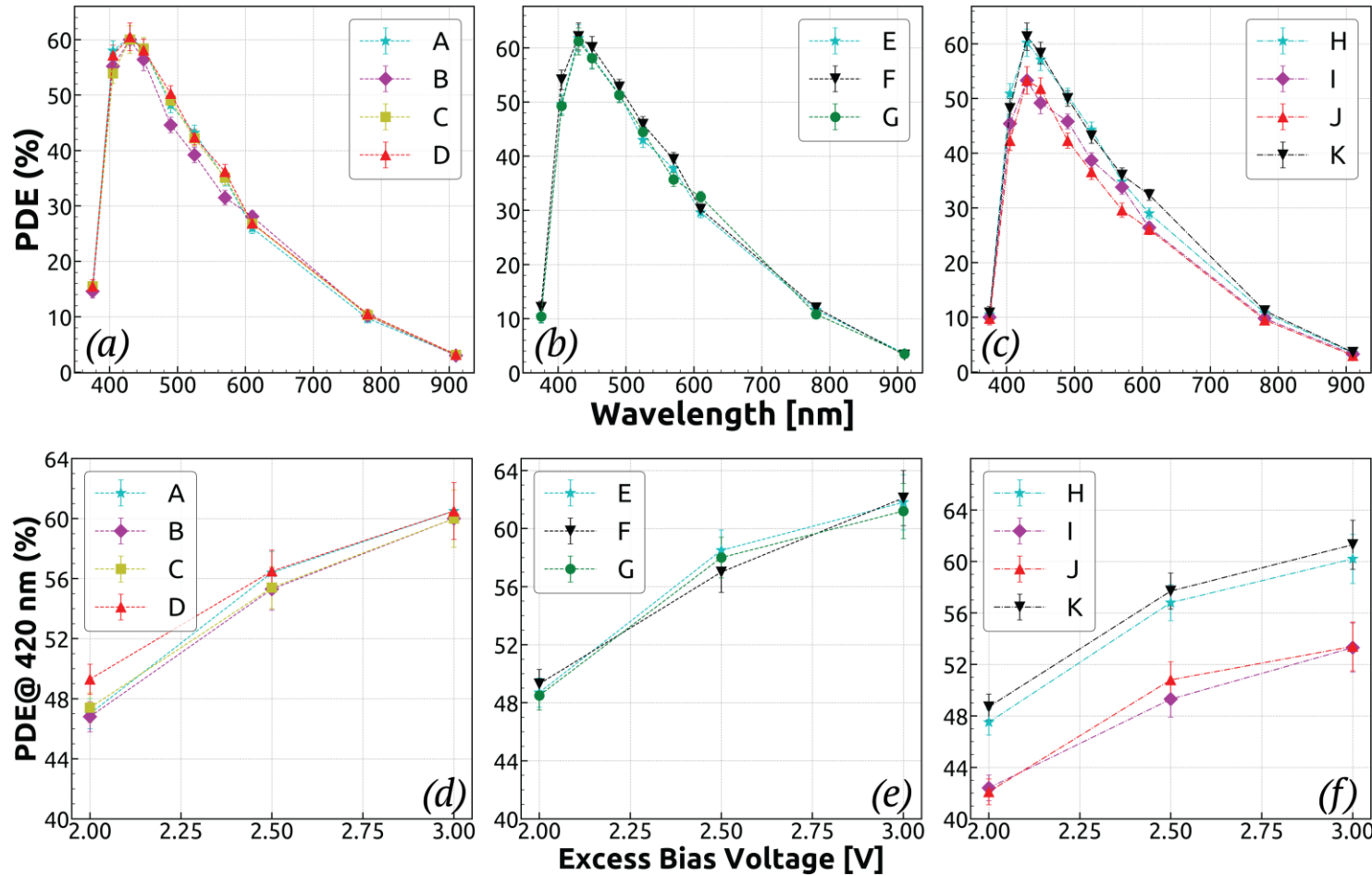
63% @ 420 nm 110 nm CMOS (2024)

N. D'Ascenzo, *IEEE Electron Device Letters*, 2019

N. D'Ascenzo, *submitted to IEEE Trans. Elec. Dev.*, 2024

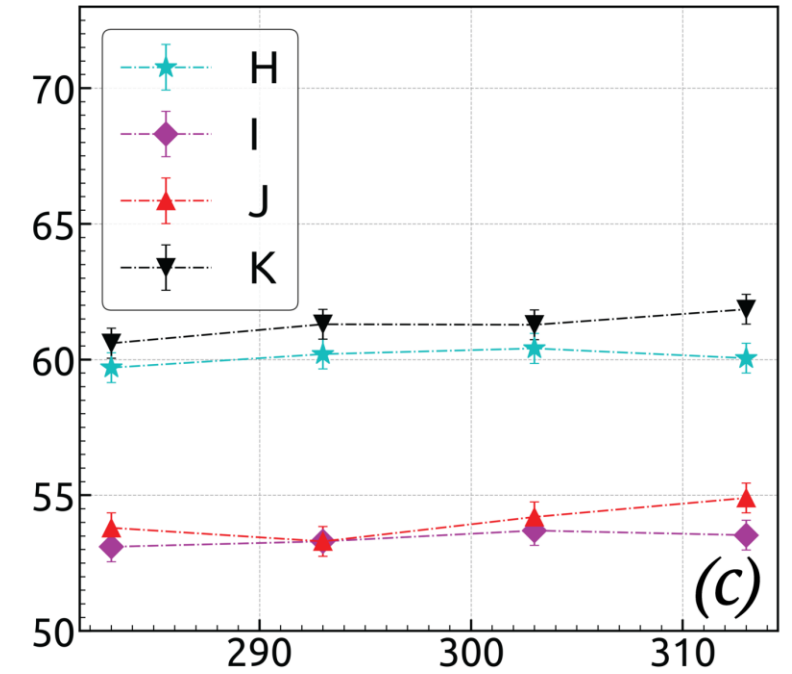
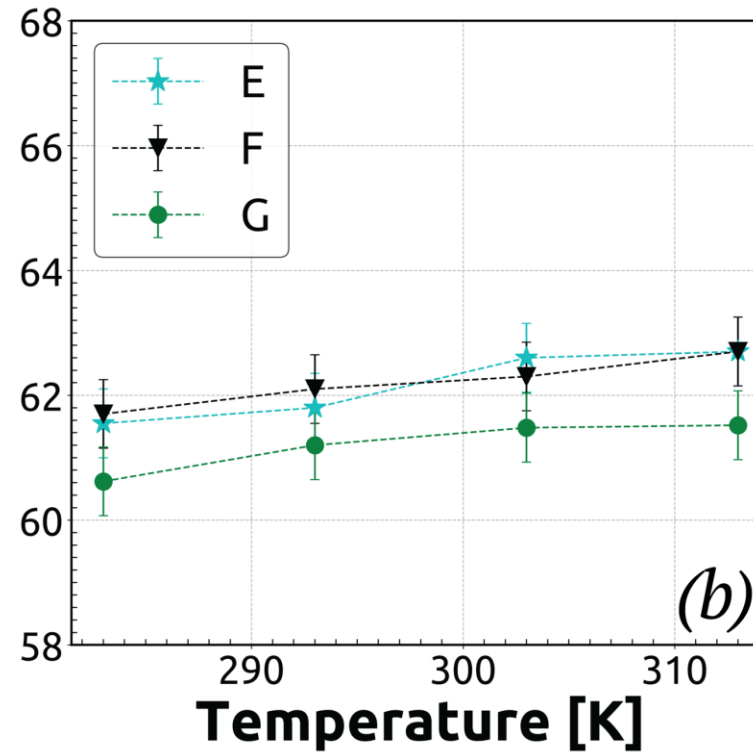
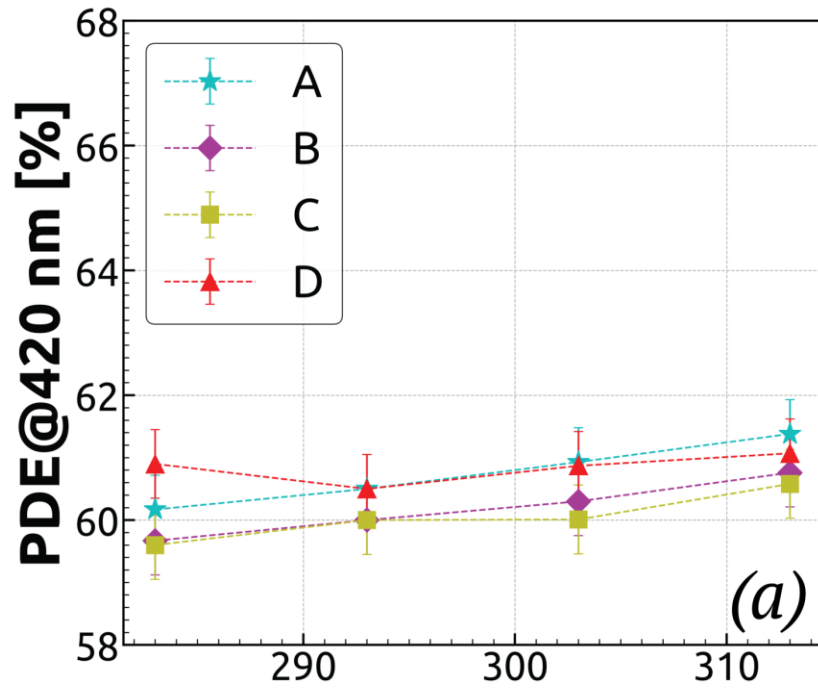


## Several layout variations confirmed the correct dependence of the PDE on the excess bias voltages



N. D'Ascenzo, submitted to IEEE Trans. Elec. Dev., 2024

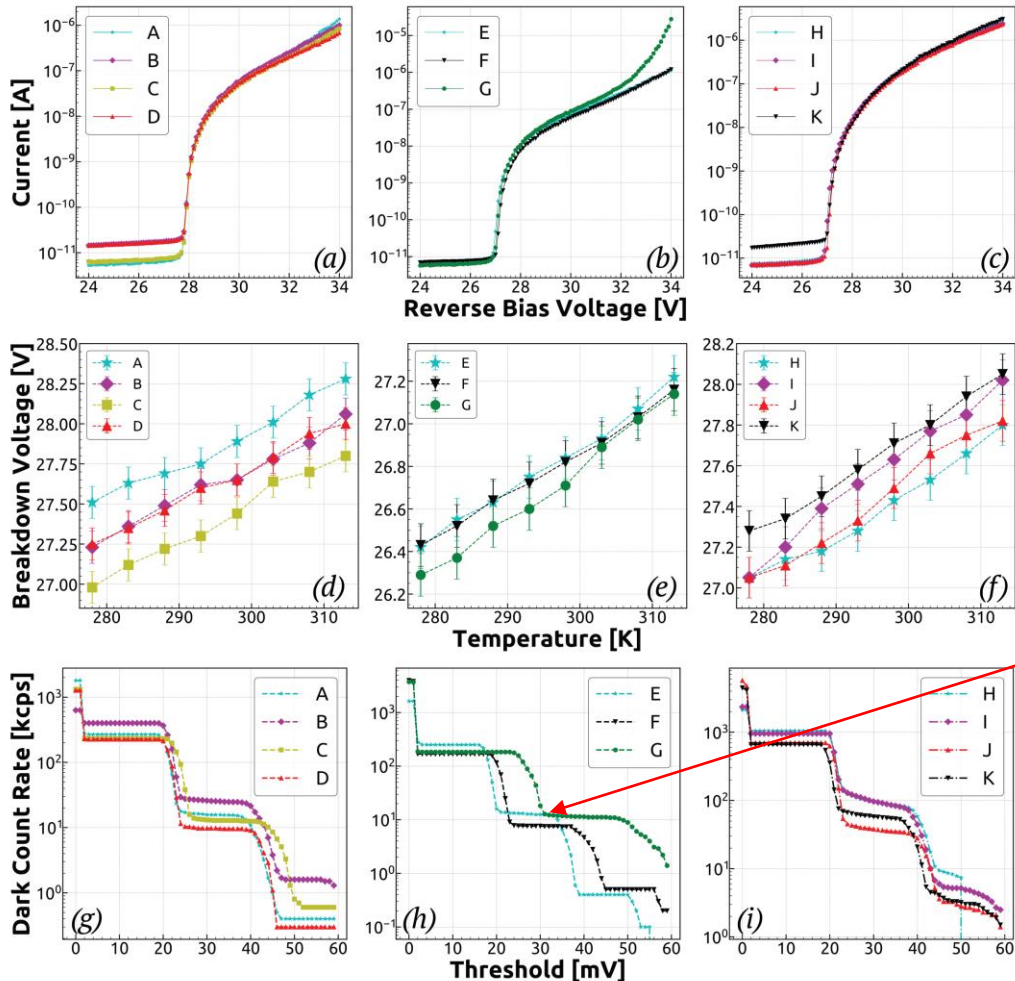
No significant trend of the PDE over the temperature is observed



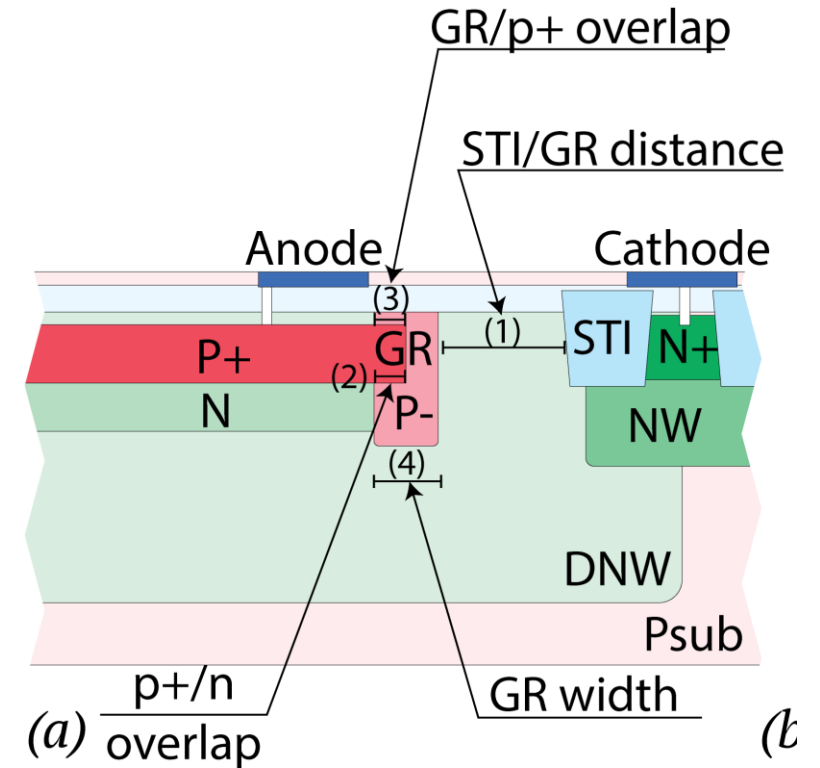
N. D'Ascenzo, submitted to IEEE Trans. Elec. Dev., 2024

# Noise characterization

The STI fabrication process causes a rise in the density of deep-level carrier generation centers at its interface



174 kcps/mm<sup>2</sup>

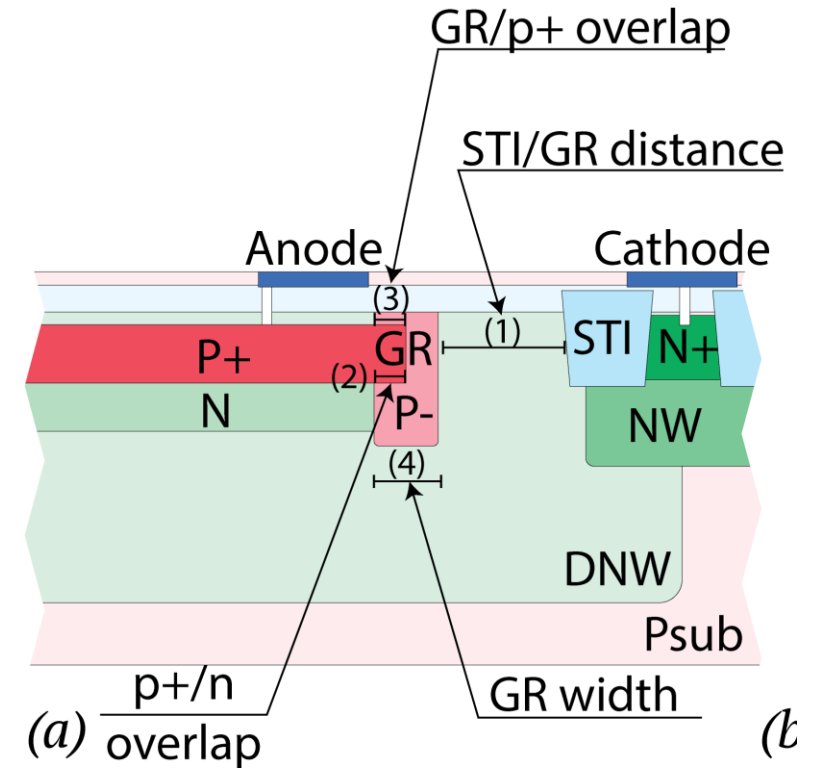
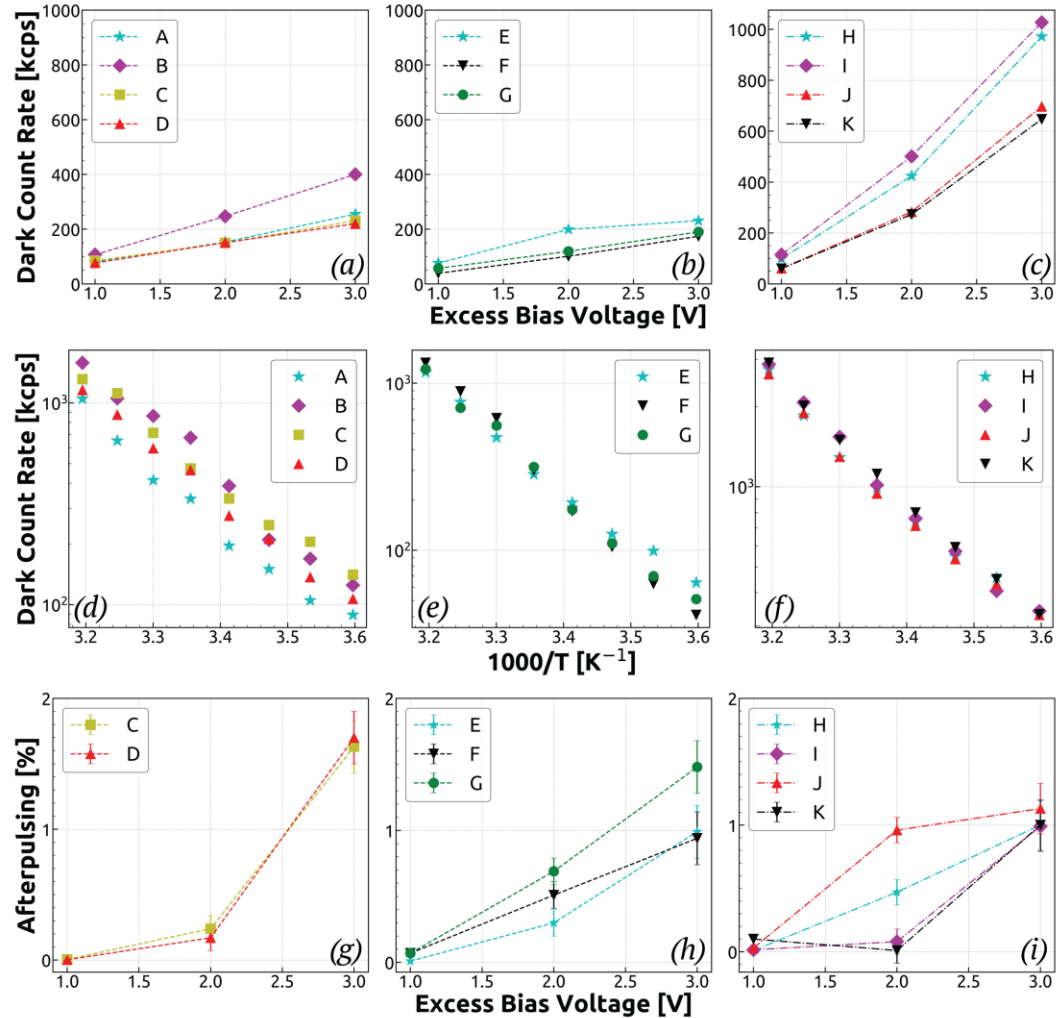


Breakdown voltage over temperature coefficient ( $23 \pm 1$ ) mV/K

# Dark count rate



## Temperature and voltage dependence of the dark count rate as expected

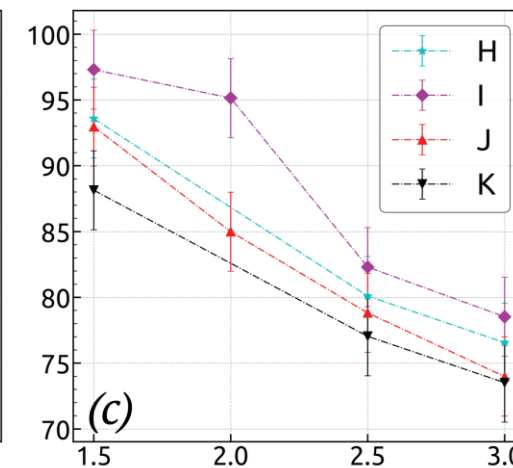
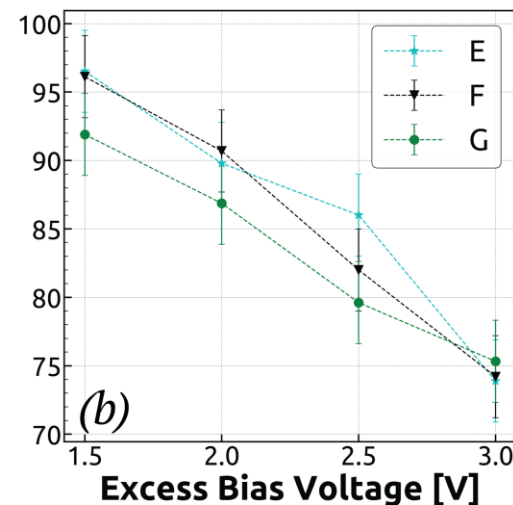
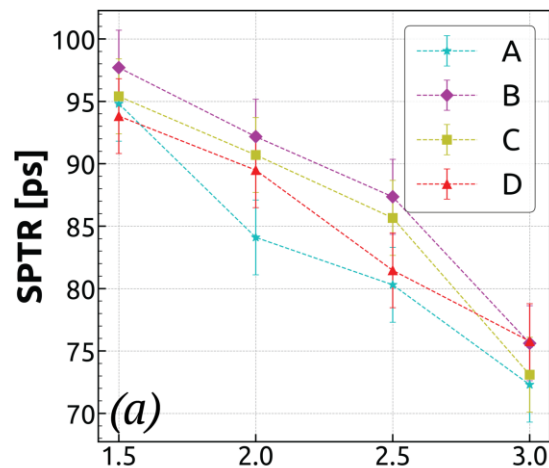
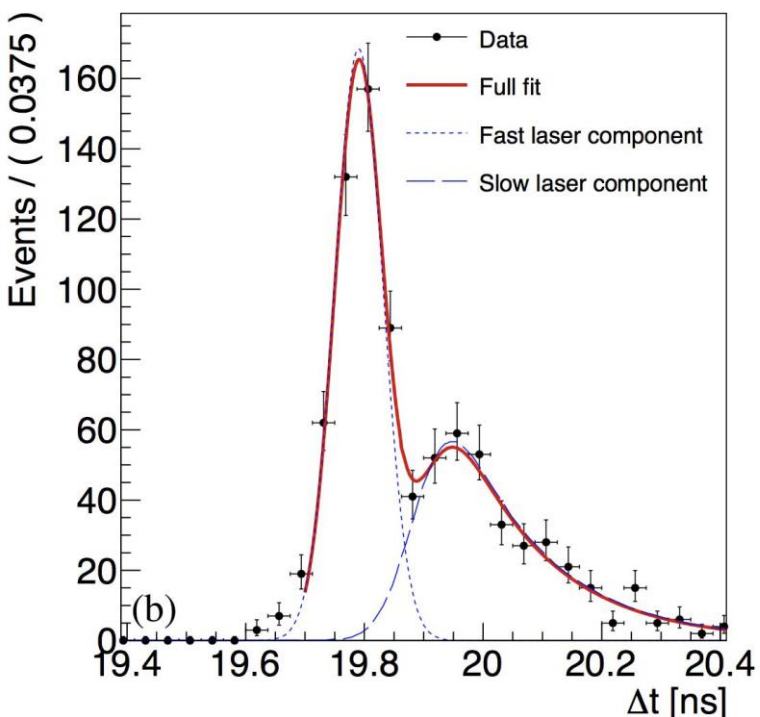


N. D'Ascenzo, submitted to IEEE Trans. Elec. Dev., 2024

# Single Photon Timing

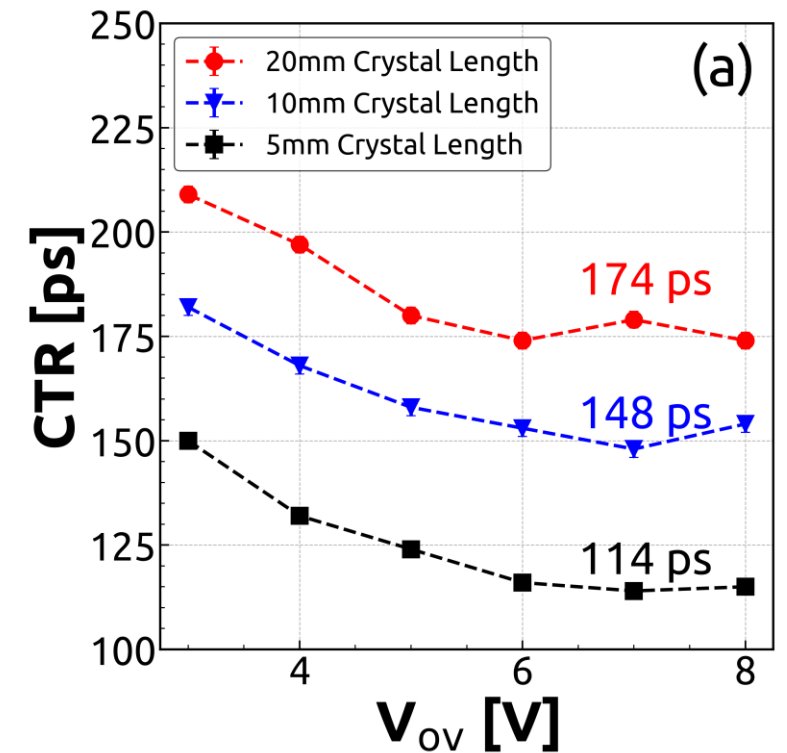
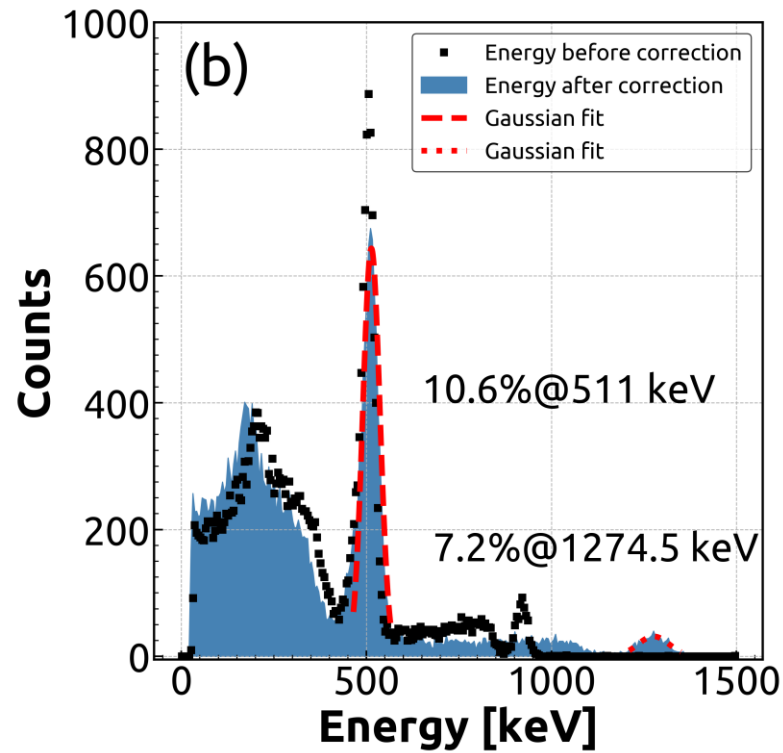
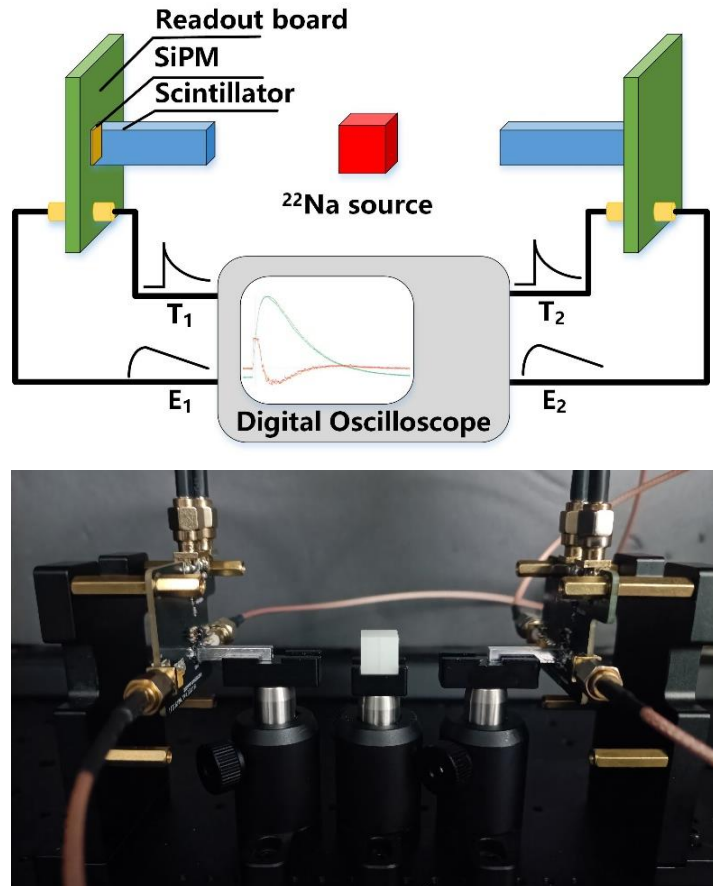


SiPM timing properties depends on the electric field strength and on the p/n junction width



Approximately 75 ps (FWHM) at 110 nm CMOS node

Energy and time resolution of the devices are consistent with the requirements of PET

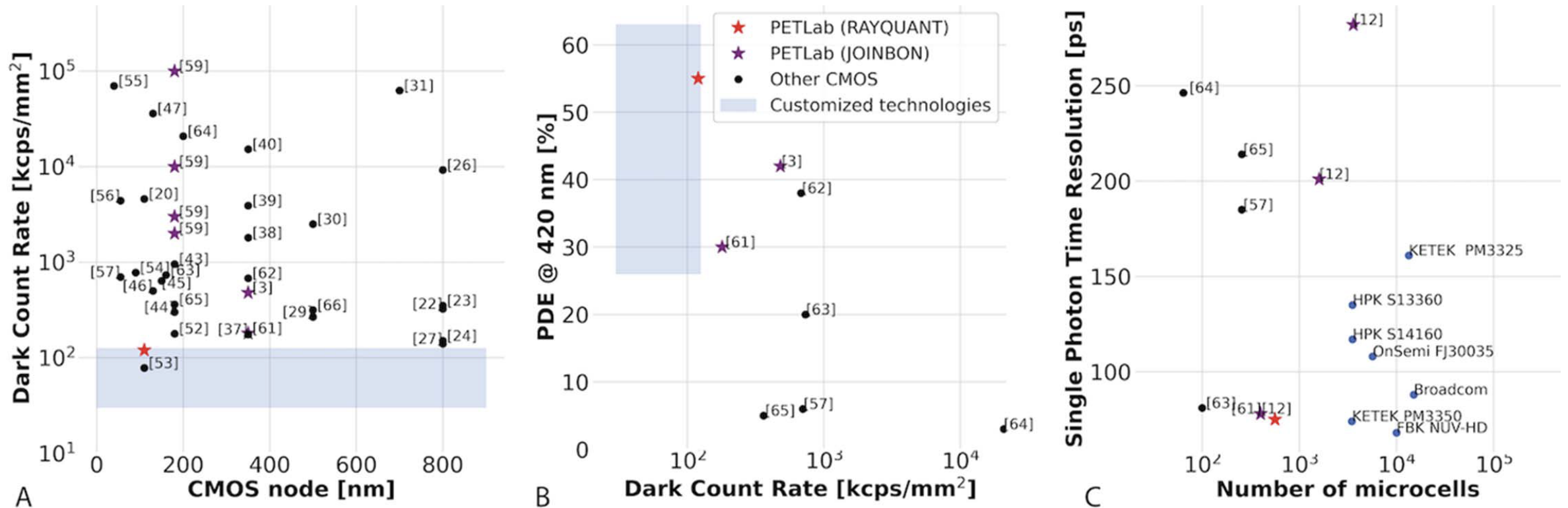


N. D'Ascenzo, submitted to IEEE TNS., 2024

# Overview of parameters

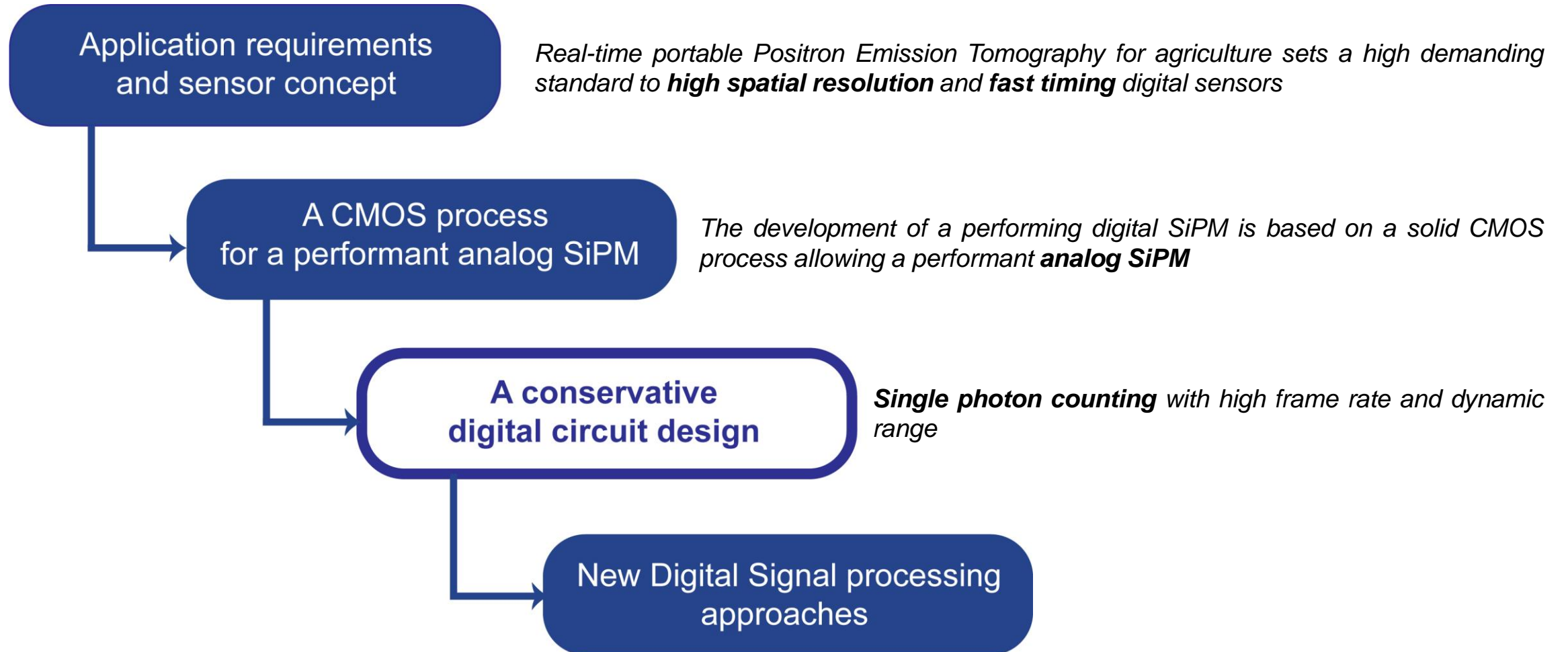


The obtained SiPM is competitive with commercial devices



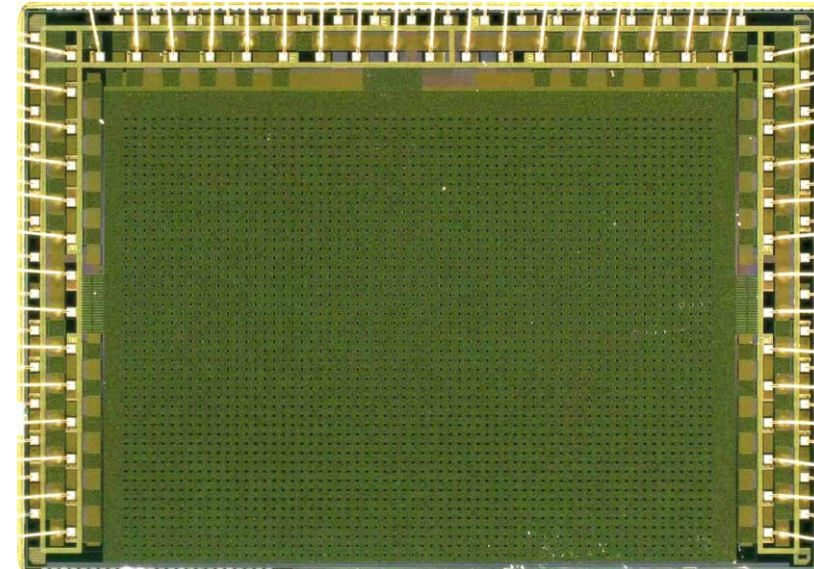
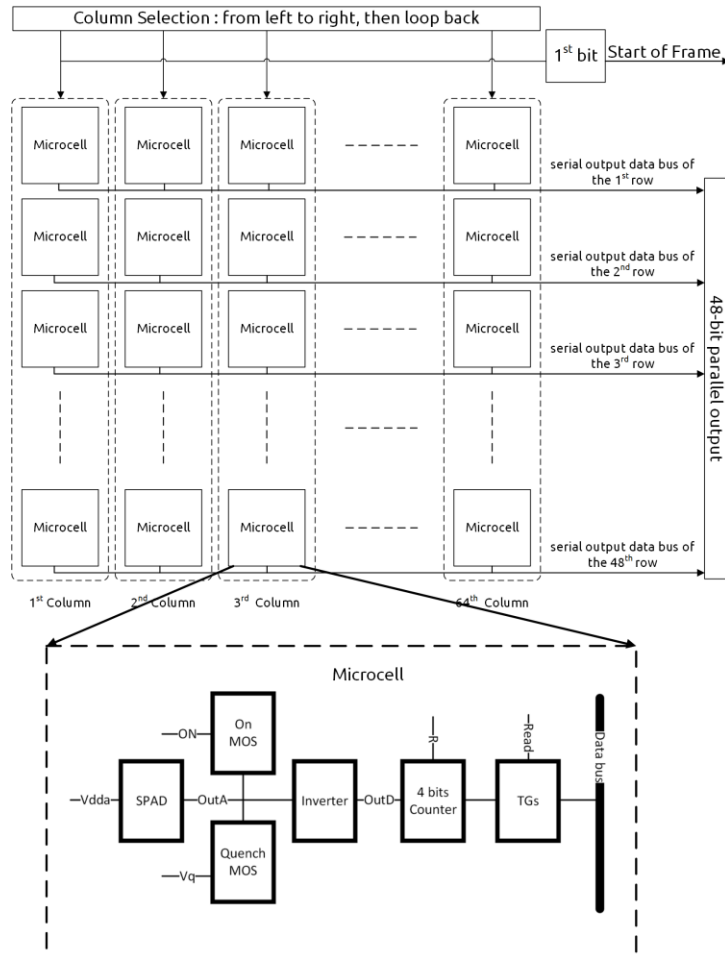
N. D'Ascenzo, Chinese Optics Letters, 2024

Being obtained at a CMOS node, it is compatible with electronics on chip





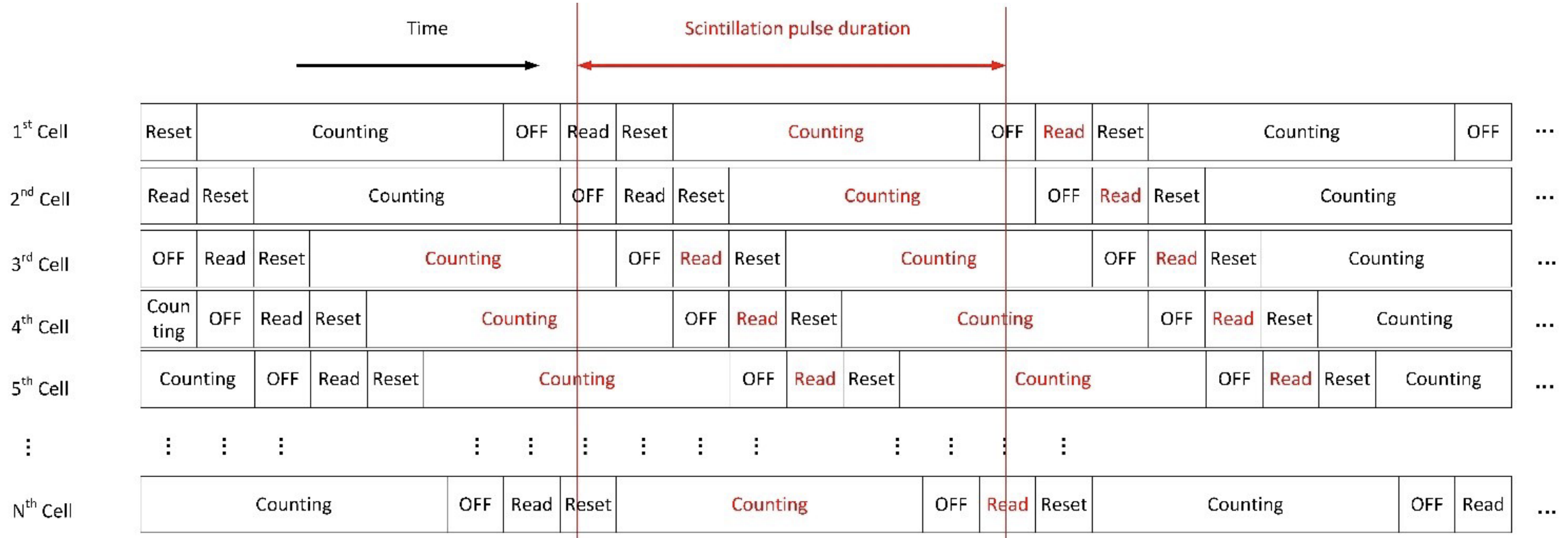
## Array of digital SPAD with single pixel readout fabricated at 350 nm CMOS



- **Pixel size:** 50x50  $\mu\text{m}^2$
- **Array size:** 48x64 (3072)
- **Die size:** 6.84x9.7  $\text{mm}^2$
- **Frame rate:** 4 MHz



## The signal pulse train – a “scintillation light camera”

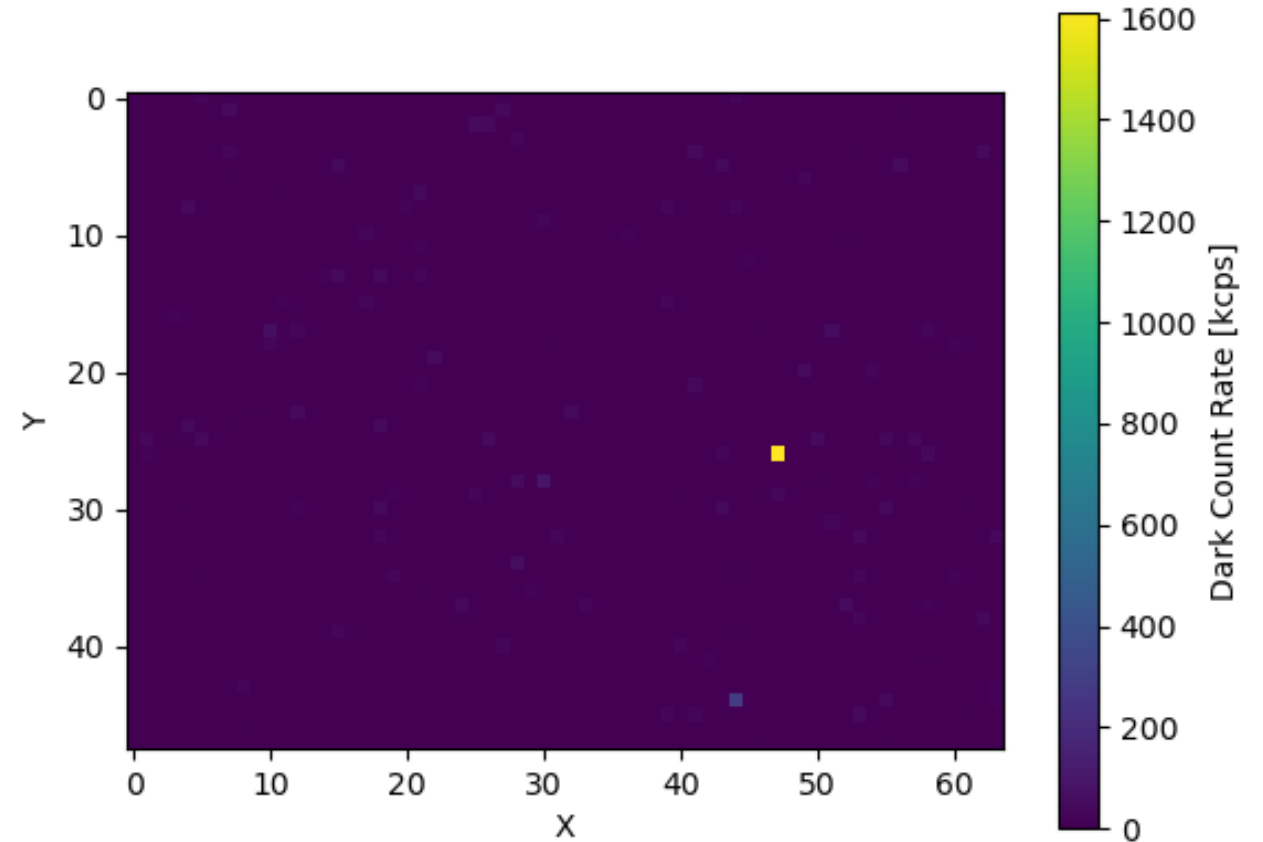
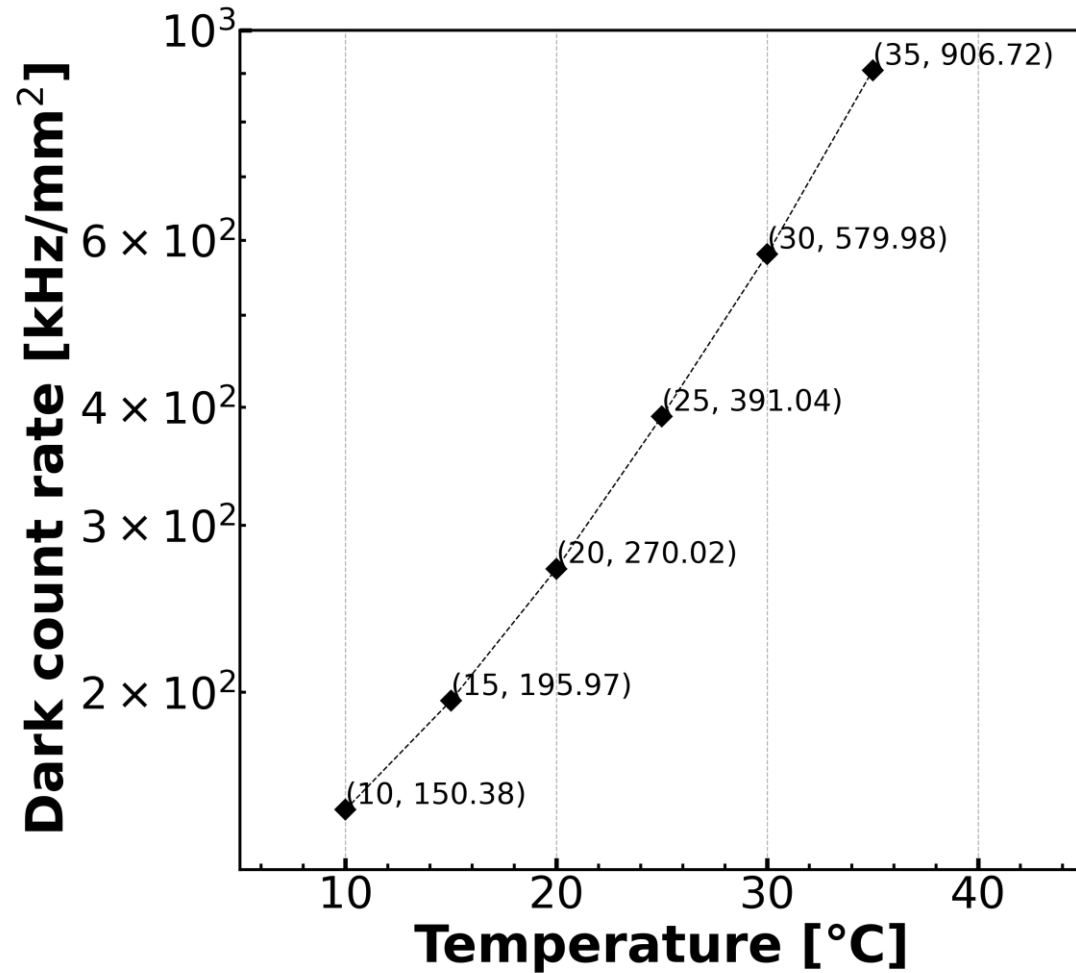


**Important – note that the arrival time information is not yet included in this version of the sensor**

# Dark count rate

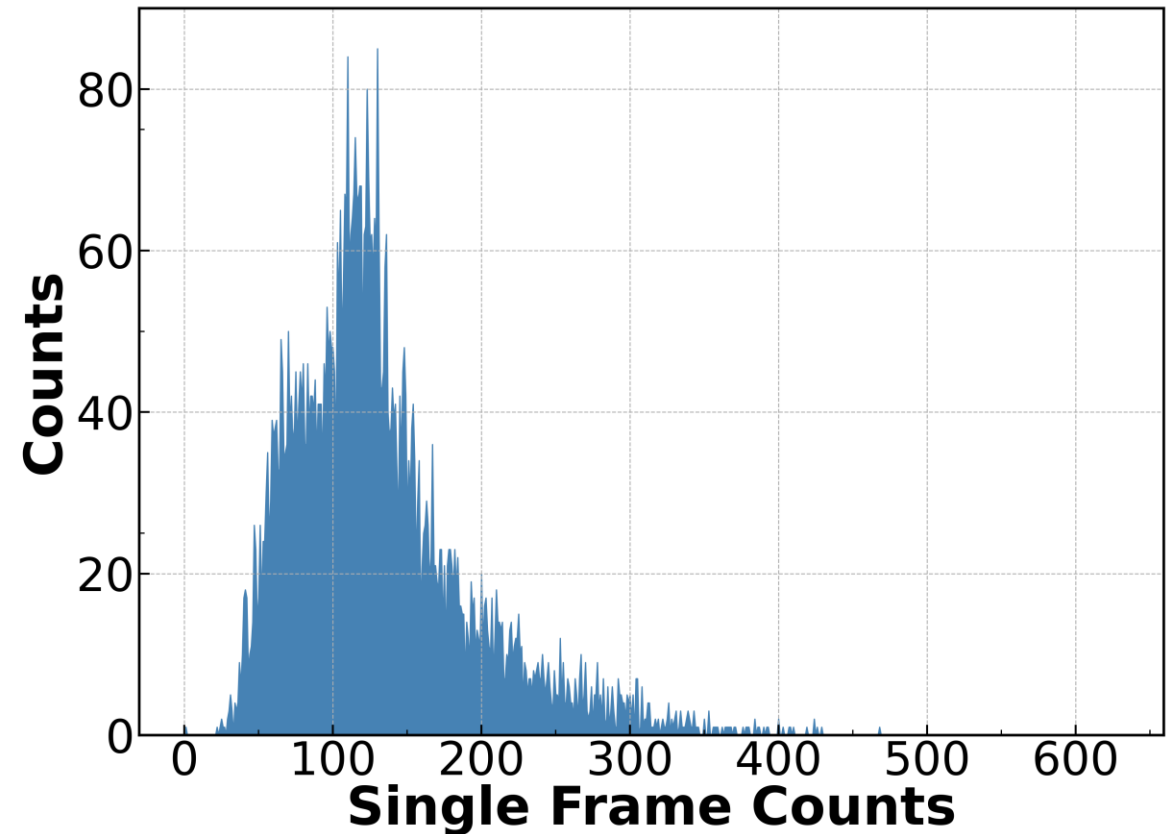
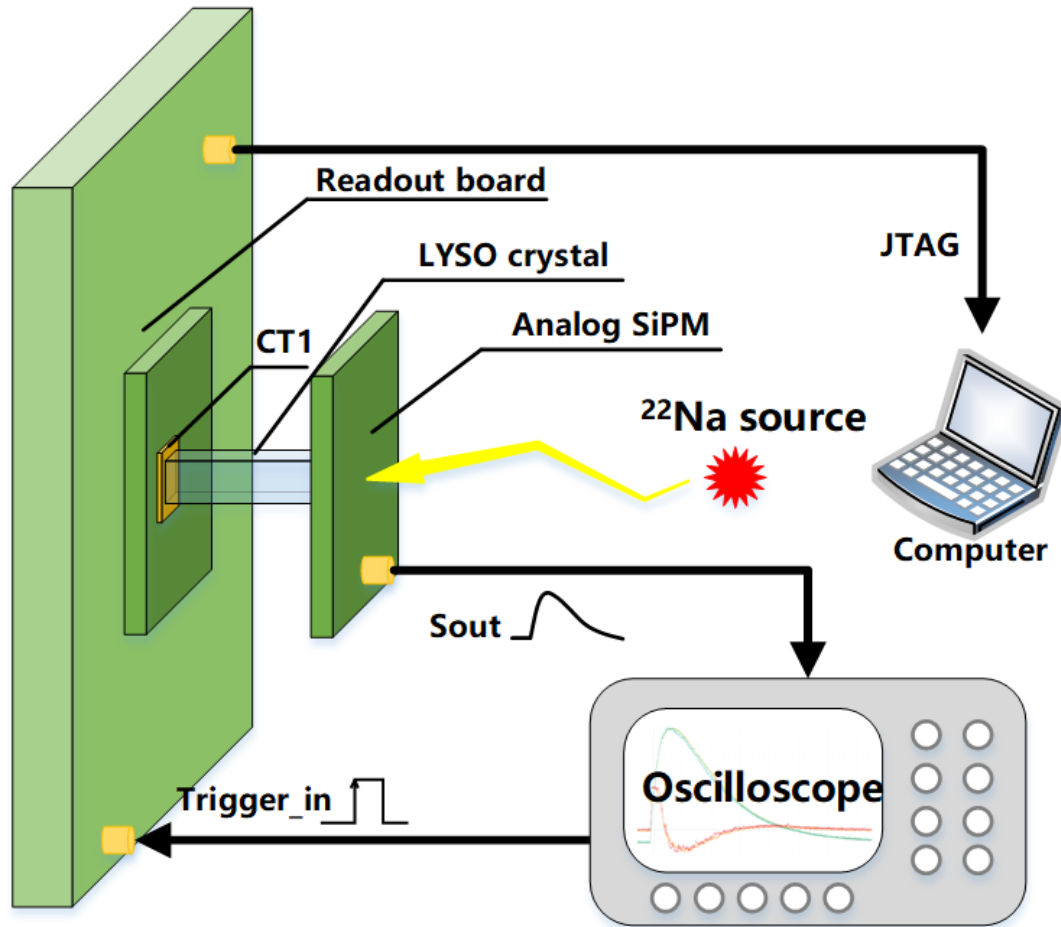


The dark count rate increases with temperature. The implementation of transistors slightly increases DCR



# Scintillator readout

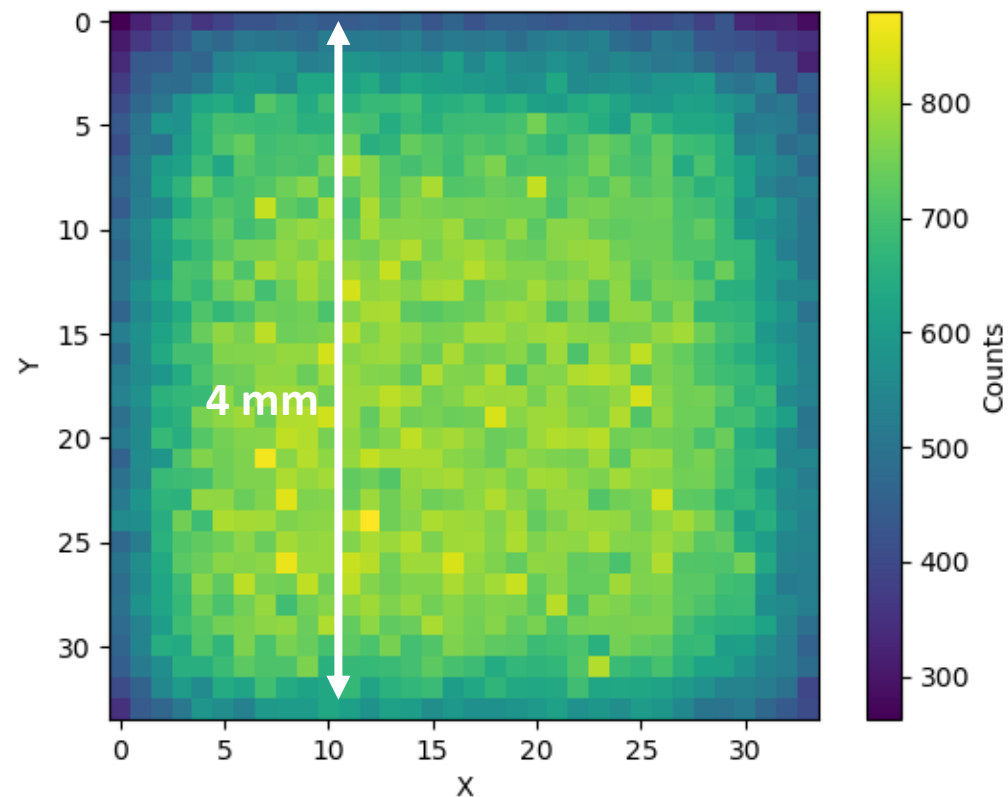
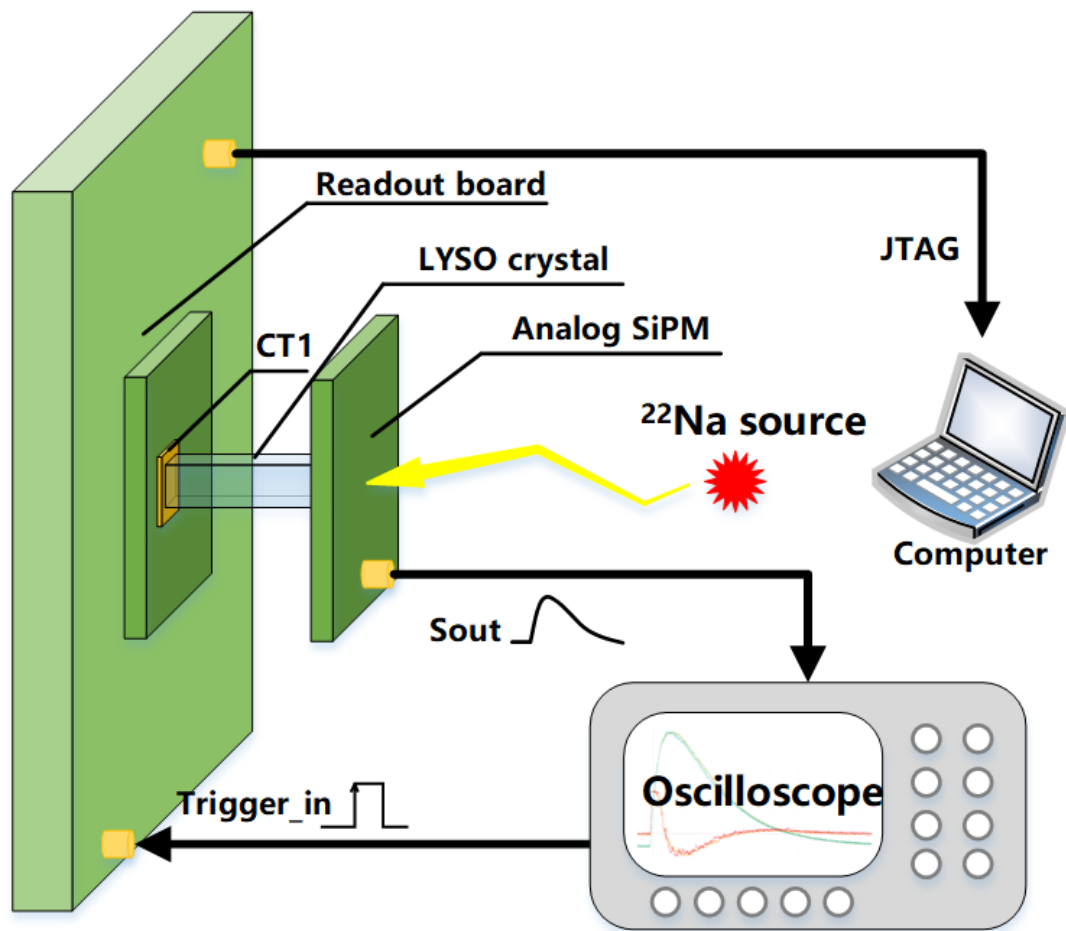
Read out the scintillation light produced by the detection of 511 keV optical photons in a 4x4 mm<sup>2</sup> LySO crystal



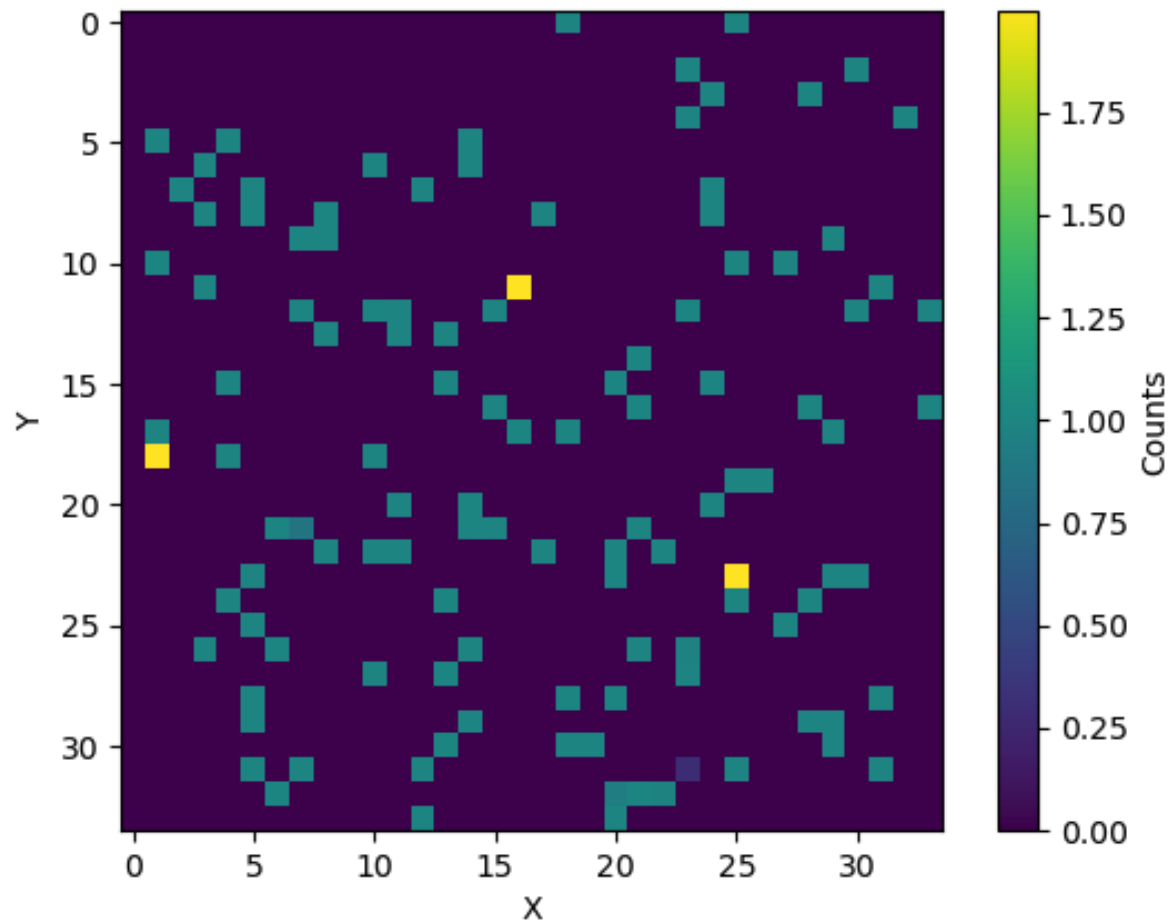
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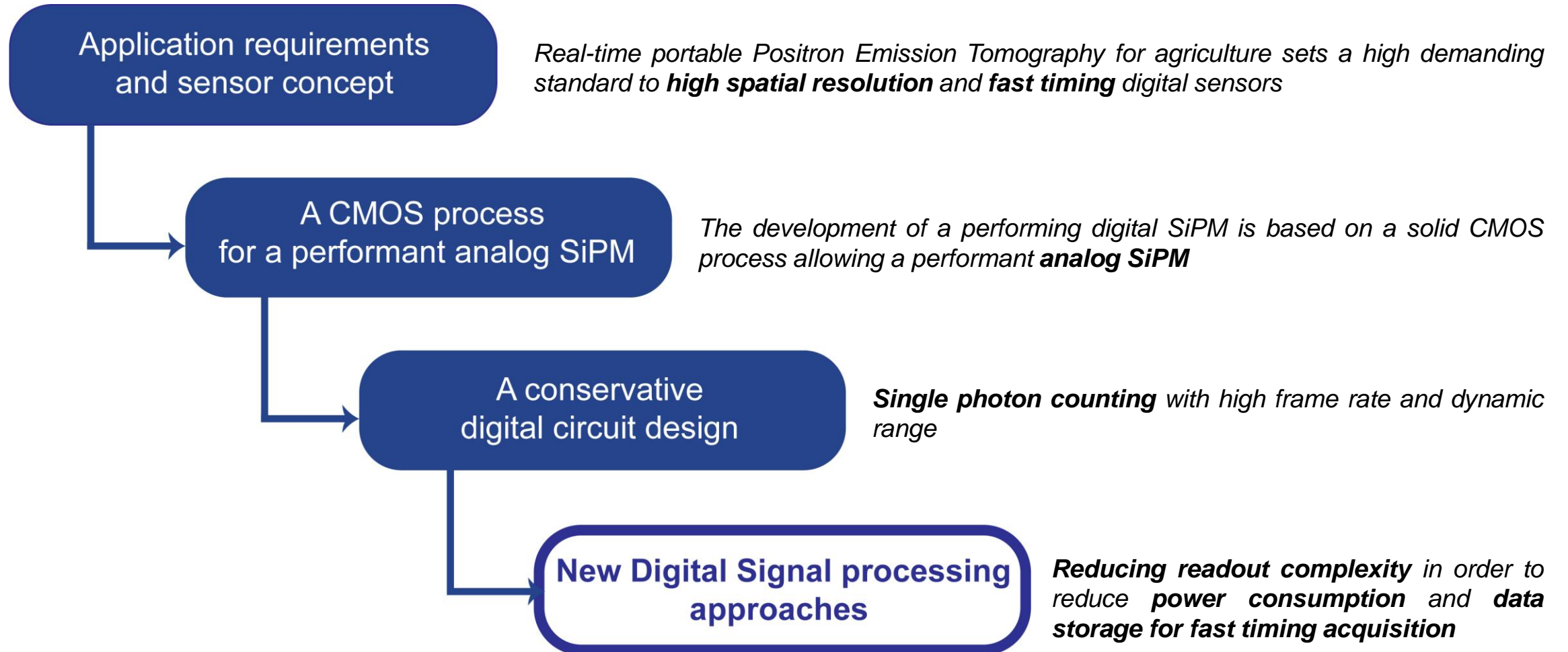


Visualize the scintillation light produced by the detection of 511 keV optical photons in a 4x4 mm<sup>2</sup> LySO crystal

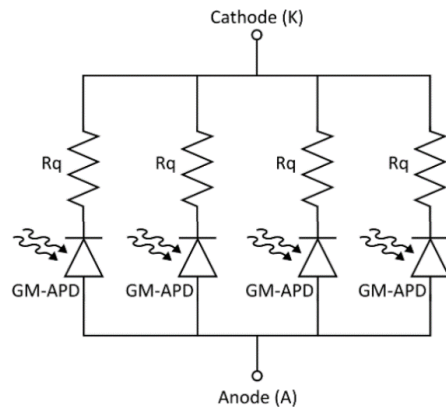
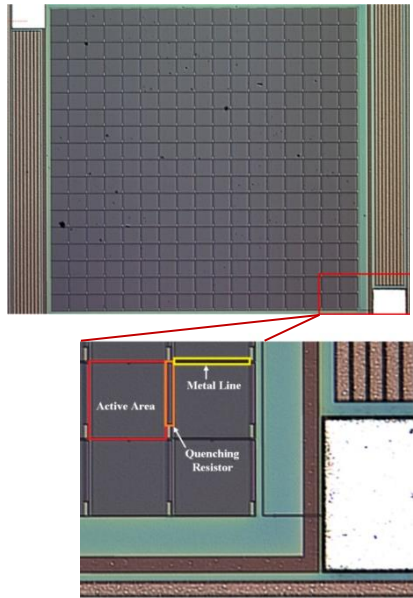


# Scintillator readout

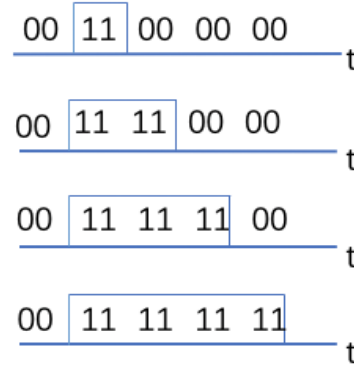




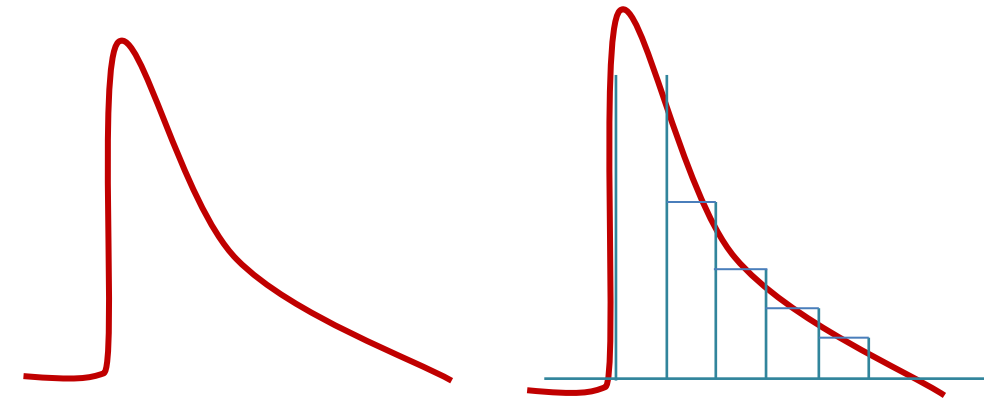
## Multiple Analog-to-Digital Conversions Limit Current SiPM's Performance



MC working in Geiger mode



Hundreds of **digital** signals



Add to **analog** signal output

**Redigitalisation**

Digital to Analog

Analog to Digital

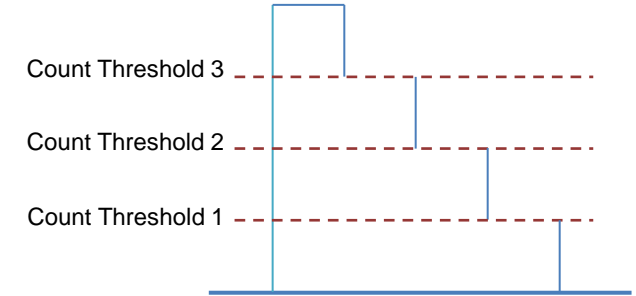
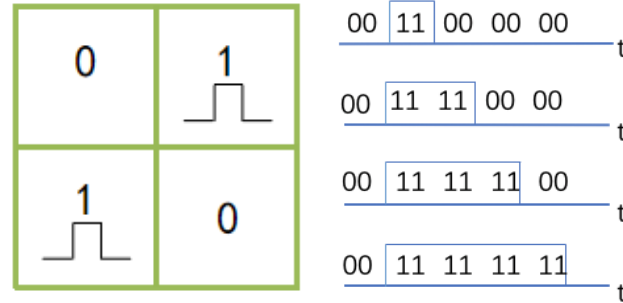
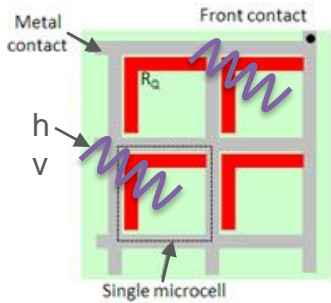
Direct digitization of SiPM is crucial

## Challenges of SiPM Digitization



A new concept – sensors under production being delivered in November 2024

Real-time digitization at the signal source addresses the challenges of digital readout.



## SiPM Receives Photons

## Digitize from the Signal Source, Generating Multiple Digital Response Signals

## Direct real-time Digitization

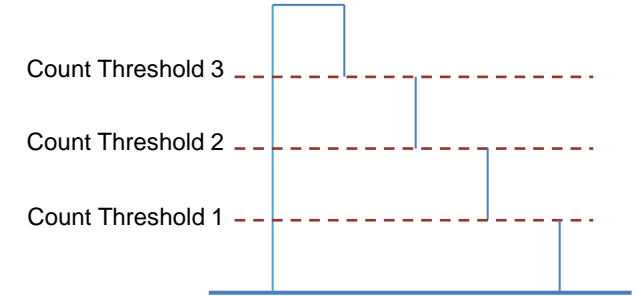
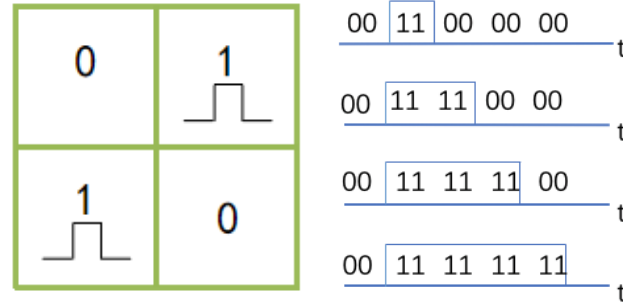
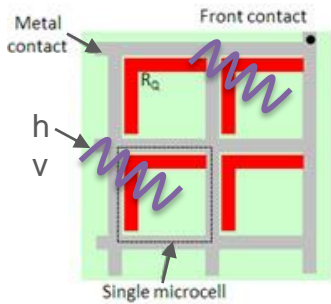
- ❑ Photon Counting Threshold Model Based on Prior Knowledge
- ❑ Digitize "count/time pair" signals to reconstruct photon timing information.
- ❑ Achieve direct real-time digitization of SiPM output signals to ensure signal integrity.

Significant leap in photodetection performance

- **Higher detection efficiency**
- **Extremely low dark count rate**
- **Faster time resolution**
- **Higher readout speed**

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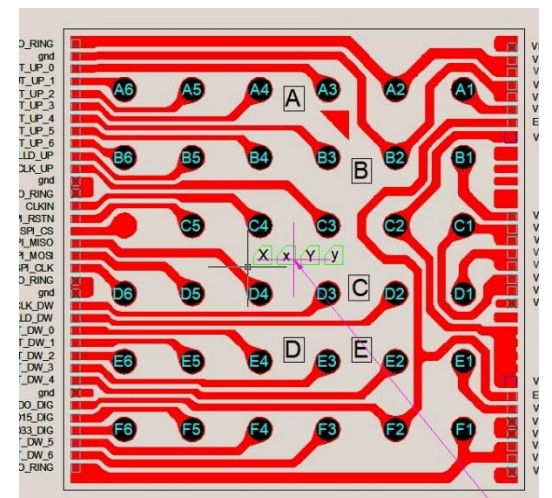
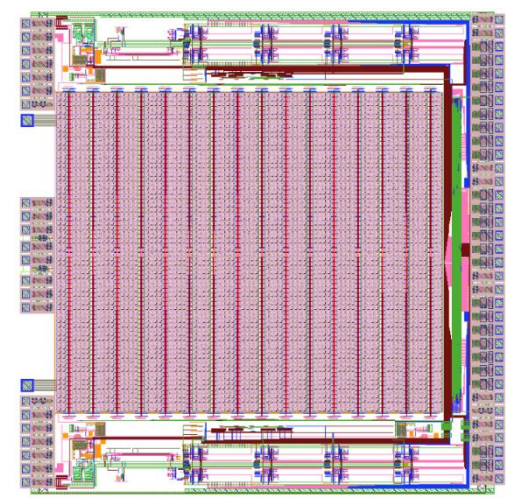
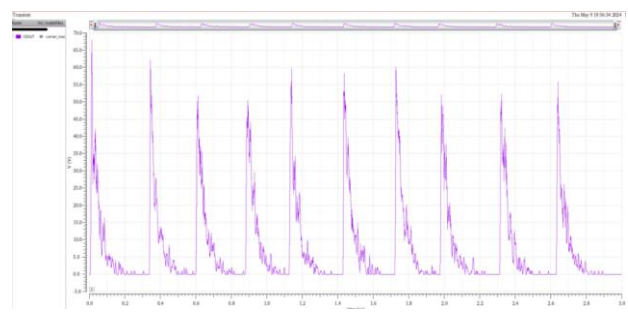
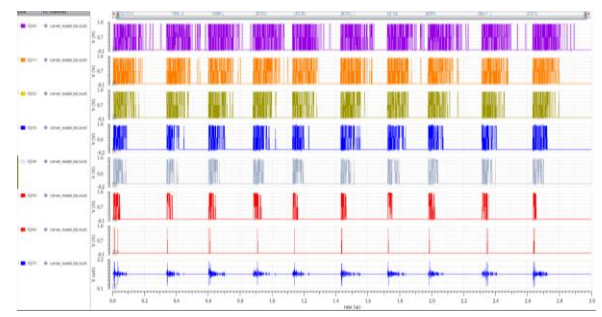
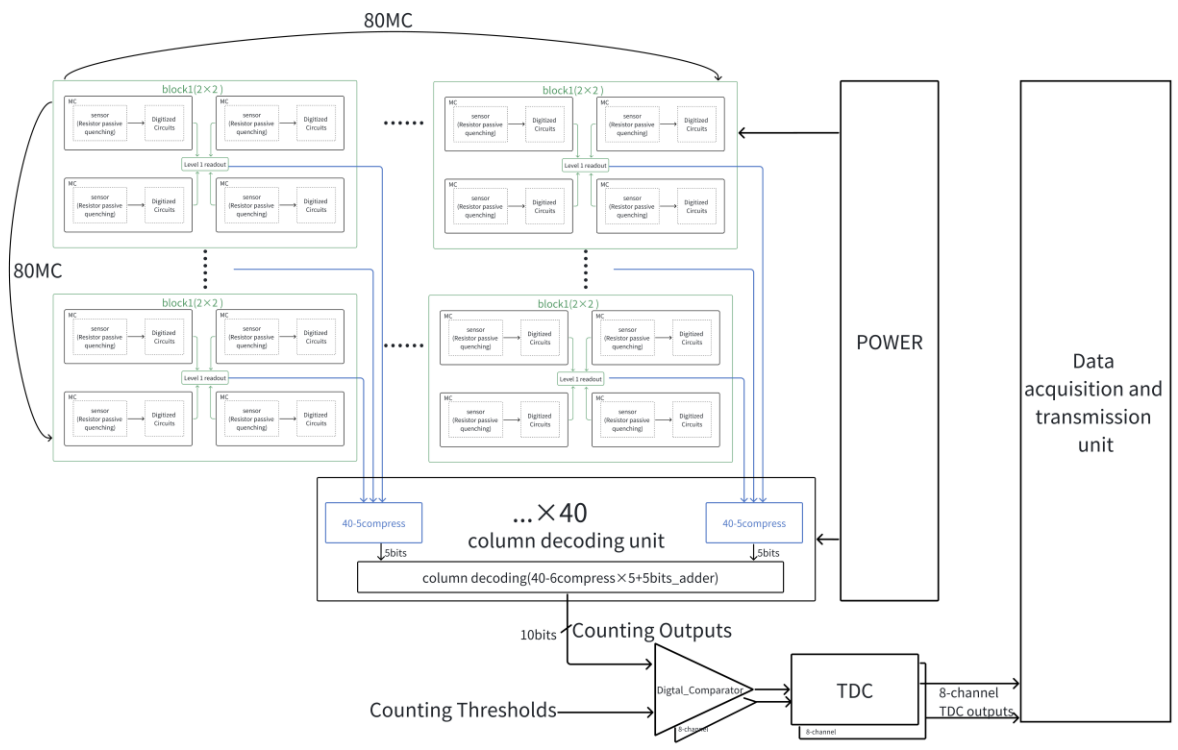
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# MT SiPM design



A PET system based on this chip will be available in 2025

Version1:4mm×4mm:bolck (2×2)





- The high time and spatial resolution required in time dynamic agricultural PET necessitates the development of new digital CMOS SiPM devices
- The digital CMOS SiPMs will have a broad application to scintillator-based sensors
- Scintillator readout with digital SiPM devices will reveal unexplored possibilities in single photon digital signal processing



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Thankyou!!